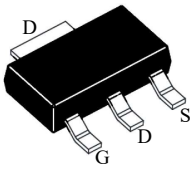
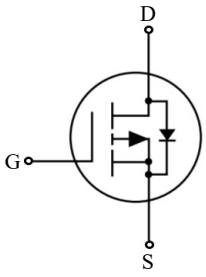
SMTQ06P700LSSEH

P-Channel Enhancement Mode Field Effect Transistor

FEATURES

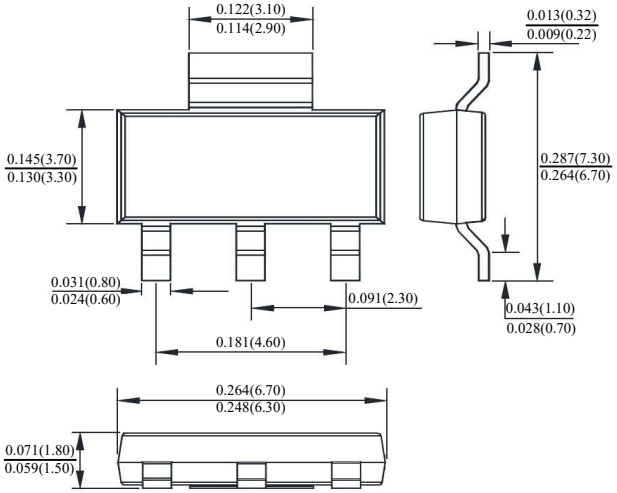
· Suffix "H" indicates Halogen-free parts, ex.SMTQ06P700LSSEH





D	Drain
G	Gate
S	Source

SOT-223



Dimensions in inch and (millimeter)

Maximum Ratings(T_A=25 ℃ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current	T_C=25℃	I_D	-9	A
	T_C=100℃		-6	
Pulsed Drain Current (Note 1)		I_{DM}	-35	A
Single-Pulse Avalanche Current		I_{AS}	-17	A
Single-Pulse Avalanche Energy (Note 2)		E_{AS}	14	mJ
Power Dissipation	T_C=25℃	P_D	12.5	W
Thermal Resistance from Juntion to Ambient (Note 3)		$R_{\theta JA}$	50	℃/W
Thermal Resistance from Juntion to Case		$R_{\theta JC}$	10	℃/W
Operating and Storage Temperature Range		T_J ,T_{stg}	- 55 to + 150	℃

Note :

1. Pulse width≤100μs, Duty Cycle≤2%, Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150℃
2. Limited by $T_{J(MAX)}$, starting T_J=25°C, L=0.1mH, R_g=25Ω , I_{AS}=-17A, V_{GS}=-10V.
3. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate in still air.

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Electrical Characteristics(T_A=25 ℃ unless otherwise specified)

Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Static						
Drain Source Breakdown Volta	I_D=-250μA	V_{DSS}	-60	-	-	V
Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	$V_{GS(th)}$	-1.2	-	-2.5	V
Zero Gate Voltage Drain Current	V_{DS}=-48V	I_{DSS}	-	-	-1	μA
Gate-Body Leakage Current	V_{GS}=±20V	I_{GSS}	-	-	±0.1	μA
Drain-Source On-State Resistance	V_{GS}=-10V, I_D=-5.7A V_{GS}=-4.5V, I_D=-4.4A	$R_{DS(on)}$	- -	70 -	90 110	mΩ
Dynamic						
Forward Transfer Admittance	V_{DS}=-15V, I_D=-5.7A	g_{FS}	-	5	-	S
Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	R_g	-	7	-	Ω
Total Gate Charge	V_{DS}=-30V, I_D=-5.7A, V_{GS}=-4.5V	Q_g	-	7	-	nC
	V_{DS}=-30V, I_D=-5.7A, V_{GS}=-10V		-	16	-	
Gate-Source Charge		Q_{gs}	-	4	-	
Gate-Drain Charge		Q_{gd}	-	3	-	
Input Capacitance	V_{DS}=-30V, V_{GS}=0V, f=1MHz	C_{iss}	-	950	-	pF
Output Capacitance		C_{oss}	-	51	-	
Reverse Transfer Capacitance		C_{rss}	-	19	-	
Turn-On Delay Time	V_{GS}=-10V, V_{DD}=-30V, I_D=-5.7A, R_g=4.7Ω	$t_{d(on)}$	-	9	-	ns
Turn-On Rise Time		t_r	-	11	-	
Turn-Off Delay Time		$t_{d(off)}$	-	14	-	
Turn-Off Fall Time		t_f	-	3	-	
Drain-Source Body Diode						
Drain-Source Diode Forward Voltage	V_{GS}=0V, I_S=-1A	V_{SD}	-	-	-1.2	V
Diode Continuous Forward Current	-	I_S	-	-	-9	A
Diode Pulse Current		I_{SM}	-	-	-35	A
Reverse Recovery Time	I_S=-5.7A, di/dt=100A/μs	t_{rr}	-	13	-	ns
Reverse Recovery Charge		Q_{rr}	-	9	-	nC

RATINGS AND CHARACTERISTIC CURVES

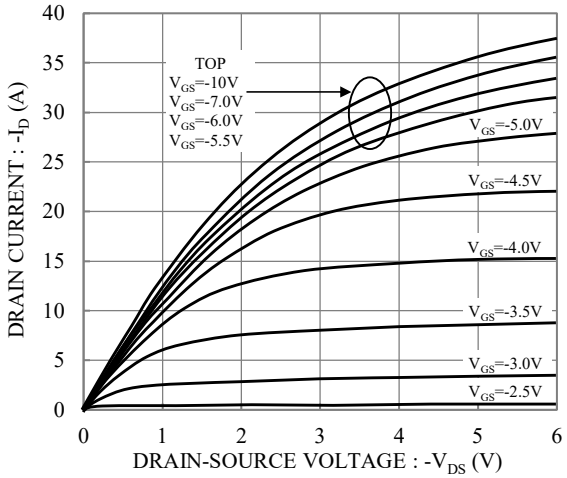

Fig.1 Typical Output Characteristics

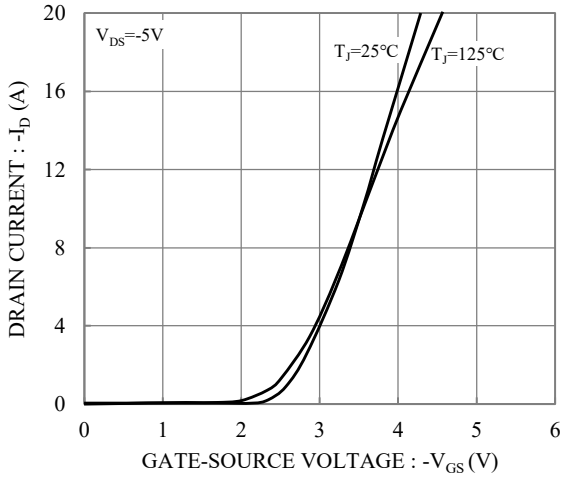

Fig.2 Typical Transfer Characteristics

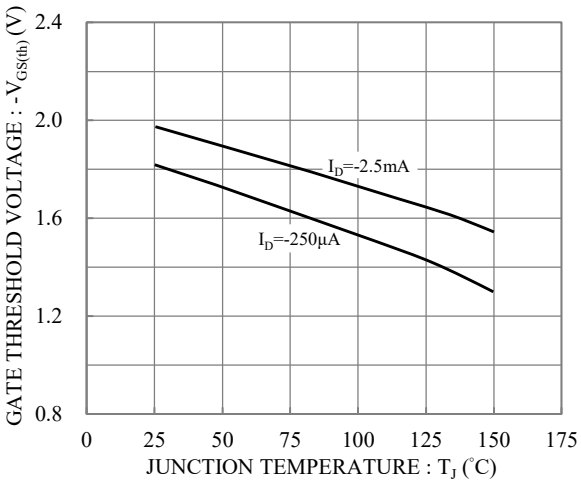

Fig.3 Gate Threshold Voltage vs. Junction Temperature

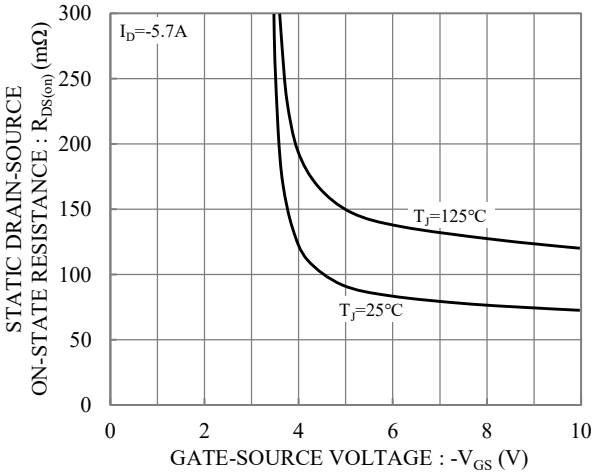

Fig.4 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

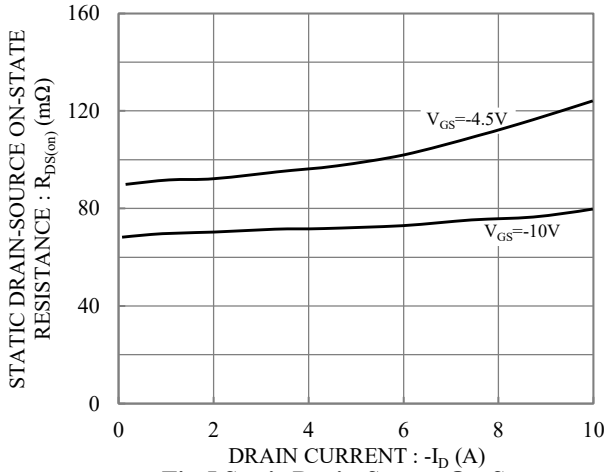

Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

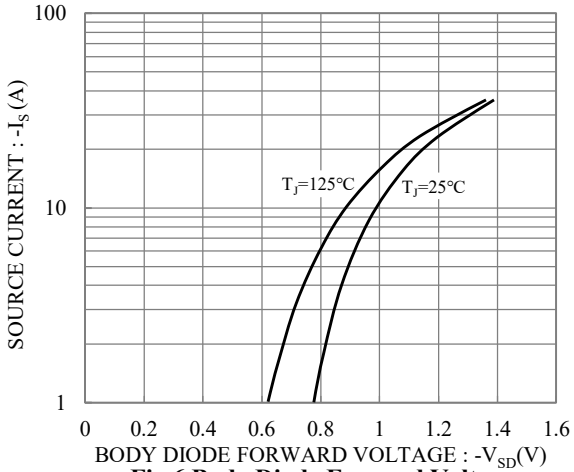

Fig.6 Body Diode Forward Voltage vs. Source Current

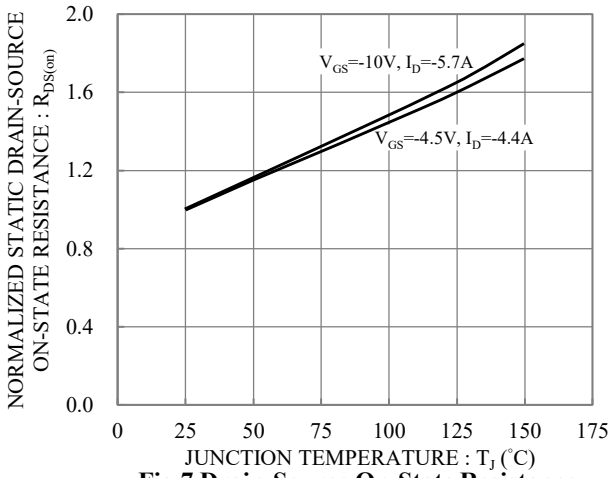

Fig.7 Drain-Source On-State Resistance vs Junction Tempearture

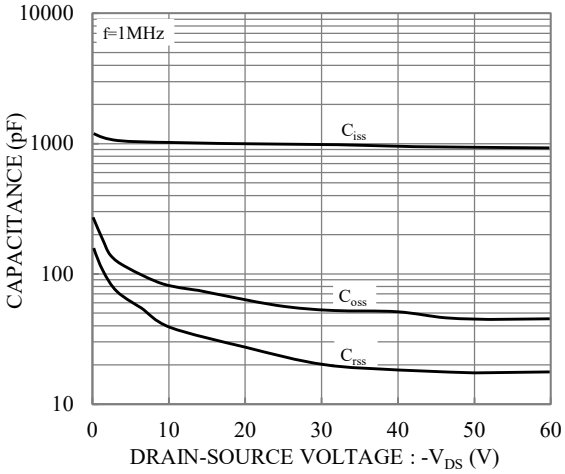

Fig.8 Capacitance vs Drain-Source Voltage

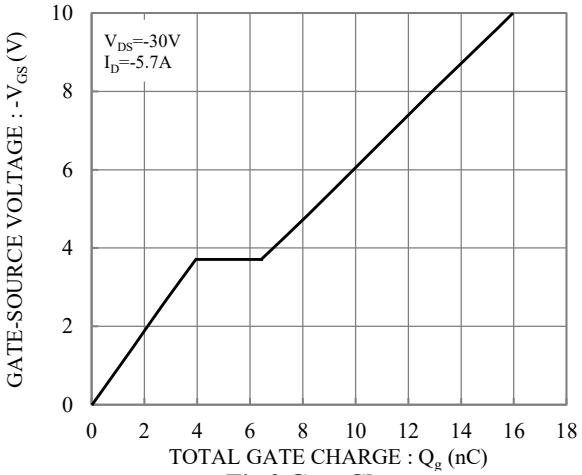

Fig.9 Gate Charge

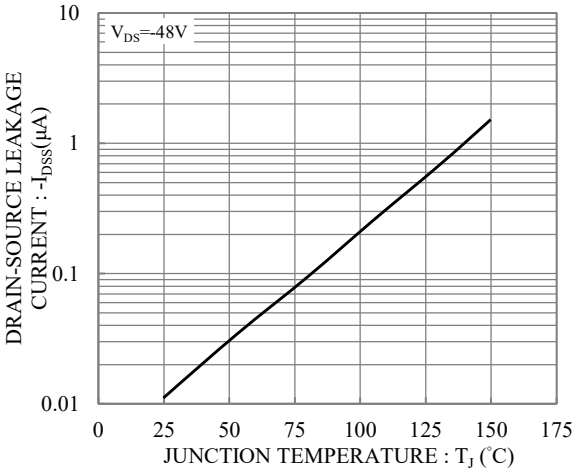

Fig.10 Drain-Source Leakge Current vs. Junction Temperature

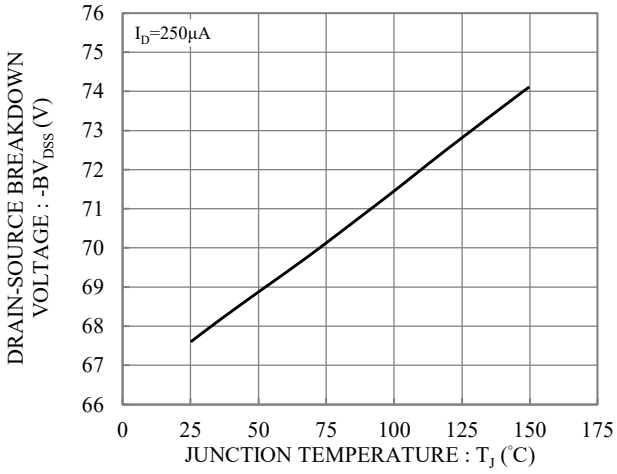

Fig.11 Brekdown Voltage vs. Junction Temperature

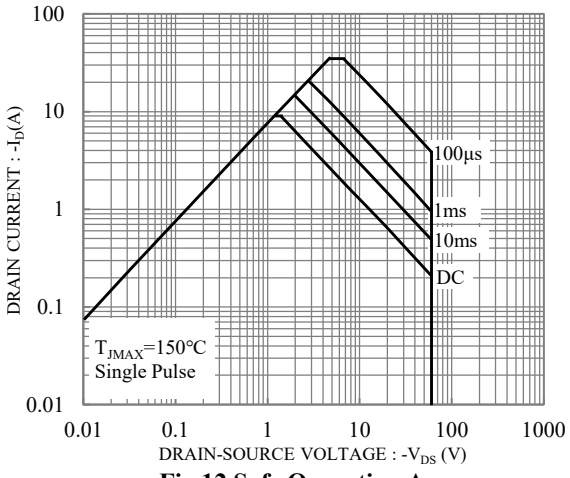

Fig.12 Safe Operation Area

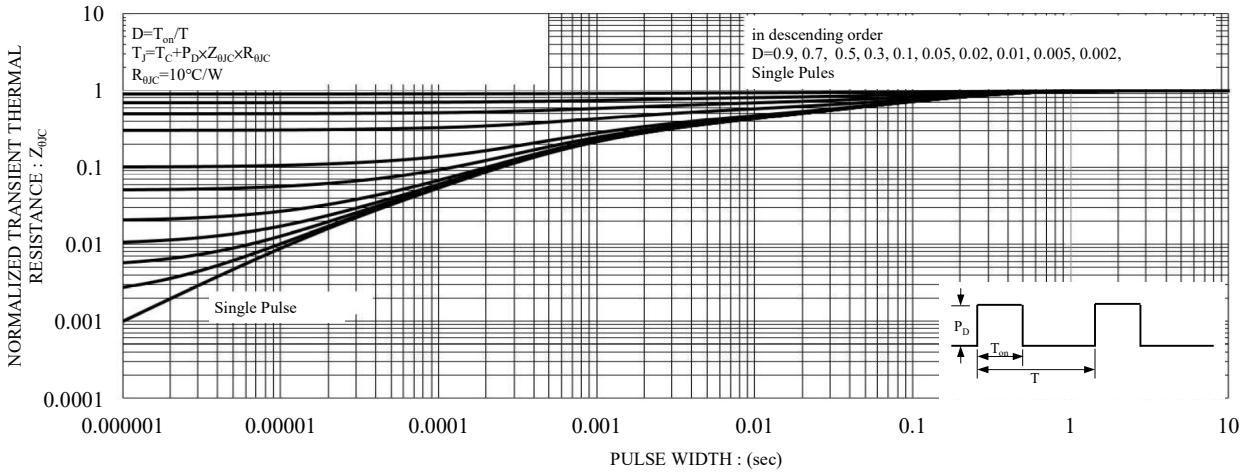

Fig.13 Maximum Transient Thermal Impedance

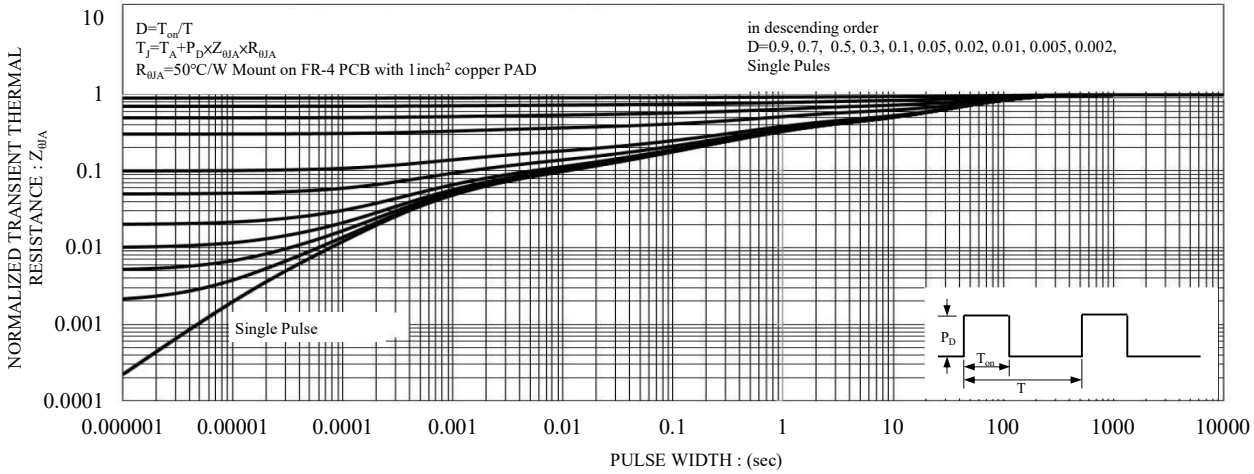

Fig.14 Maximum Transient Thermal Impedance